

REMARKS

Claims 1-12 are pending in this application. By this Amendment, claims 1 and 8 are amended for clarity, consistency and to even more clearly distinguish over the applied references, and claims 2-5 and 10 are amended for clarity and consistency. The amendments are supported in the specification by at least paragraph [0050], and Figs. 3, 5 and 7.

Applicants appreciate the courtesies extended to Applicants' representative at the May 2, 2006 personal interview.

The Office Action rejects claims 1-3 and 5-12 under 35 U.S.C. §103(a) over Zhang ("Zhang I") (U.S. Patent No. 6,633,359) in view of Murade (U.S. Patent No. 6,297,862); and claim 4 under 35 U.S.C. §103(a) over Zhang I in view of Murade and further in view of Zhang ("Zhang II") (U.S. Patent No. 5,717,224). The rejections are respectfully traversed.

Zhang I fails to disclose a liquid crystal device or active matrix substrate having a plurality of pixel regions having thin-film transistors formed of P-type transistors, a capacitance line extending in parallel to scanning lines, semi-conductor layers extended substantially to the center of each of the plurality of pixel regions so as to form a capacitance electrode, and a storage capacitor formed in a portion where the capacitance electrode and the capacitance line planarly overlap each other, as recited in independent claims 1 and 8.

As shown in Zhang I at Fig. 2, the Zhang I device has a display area B and a peripheral circuit area C. Zhang I at col. 10, lines 65-67, and col. 11, lines 53-67, discloses that Zhang I's pixel TFTs for display area B are n-type TFTs. Zhang I at col. 12, lines 56-58, and col. 13, lines 8-27, discloses that Zhang I's TFTs for peripheral circuit area C are both n-type and p-type TFTs. Thus, Zhang I has n-type TFTs only in the peripheral circuit area C, and not in display area B. Accordingly Zhang I fails to disclose a plurality of pixel regions each having thin-film transistors formed of P-type transistors. The other applied references fail to remedy this deficiency in Zhang I.

Zhang I also fails to disclose a capacitance line, a capacitance electrode, or a storage capacitor formed in a portion where the capacitance electrode and the capacitance line planarly overlap each other. The other applied references fail to remedy this deficiency in Zhang I.

In view of the foregoing, the applied references, alone or in combination, fail to disclose all the features recited in independent claims 1 and 8. It is respectfully requested that the rejections be withdrawn.

In view of the foregoing, it is respectfully submitted that this application is in condition for allowance. Favorable reconsideration and prompt allowance are earnestly solicited.

Should the Examiner believe that anything further would be desirable in order to place this application in even better condition for allowance, the Examiner is invited to contact the undersigned at the telephone number set forth below.

Respectfully submitted,



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